

Abstract of the Disclosure

The present invention relates to an integrated circuit having a MOS capacitor. In one embodiment, a method of forming an integrated circuit comprises forming an oxide layer on a surface of a substrate, the substrate having a plurality of isolation islands. Each isolation island is used in forming a semiconductor device. Patterning the oxide layer to expose predetermined areas of the surface of the substrate. Depositing a nitride layer overlaying the oxide layer and the exposed surface areas of the substrate. Implanting ions through the nitride layer, wherein the nitride layer is an implant screen for the implanted ions. Using the nitride layer as a capacitor dielectric in forming a capacitor. In addition, performing a dry etch to form contact openings that extend through the layer of nitride and through the layer of oxide to access selected device regions formed in the substrate.

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